

Page 1 of 13

. The state semiconductor, Inc. $MC68302\ Document$

Die 1:

#	Spec No.	Description	Spec Name UM	33MHz Min	33MHz Max
1	1	Cycle period	tcyc	30	
2	2,3	Clock pulse width	tcl,tch	15	
3	5A	EXTAL to Clock delay	tcd	2	11
4	6	Clock high to FC, address valid	tchfcadv	0	27
5	7	Clock high to Address, Data Hi-z	tchadz	1	25
6	8	Clock high to Address, FC invalid (Minimum)	tchafi	0	ı
7	9	Clock high to AS, DS asserted	tchsl	သ	15
8	11	Address, FC Valid to AS, DS Assert (read) AS assert (Write)	tafcvsl	8	-
9	12	Clock low to AS, DS negate	tclsn	ı	15
10	13	AS, DS Negated to Address FC Invalid	tshafi	8	-
11	14	AS (and DS read) width asserted	tsl	60	_
12	14A	DS width asserted, write	tdsl	30	-
13	15	AS, DS width negate	tsh	30	1
14	16	Clock high to Control Bus Hi-z	tchca	1	25
15	17	AS, DS Negated to R/W Invalid	tshrh	8	-
16	18	Clock high to R/W hi	tchrh	ı	15







Page 2 of 1

. The state semiconductor, lnc. $MC68302\ Document$

abie 1:

#	Spec No.	Description	Spec Name UM	33MHz Min	33MHz Max
17	20	Clock high to R/W lo	tchrl	ı	15
18	20A	AS Asserted to R/W Low (Write)	tasrv	ı	7
19	21	Address FC Valid to R/W Low (Write)	tafcvrl	8	-
20	22	R/W low to DS assert (write)	trasa		
21	23	Clock low to data valid	tcldo	ı	15
22	25	AS, DS Negated to Data-out invalid	tcldo	ı	15
23	26	Data-out valid to DS Asserted (Write)	tdosl	8	ı
24	27	Data in to Clock low	tdicl	4	1
25	28	AS, DS negate to DTACK negate	tshdah	0	65
26	29	AS, DS Negated to Data In invalid	tshdii	0	-
27	30	AS, DS negated to BERR negated	tshbeh	0	-
28	31	DTACK assert to Data-In valid	tdaldi	ı	25
29	22	HALT, RESET in transition time	trhr, trhf	ı	150
30	33	Clock high to BG assert	tchgl	1	15
31	34	Clock high to BG negate	tchgh	1	15
32	35	BR assert to BG assert	tbrlgl	2.5 clks	4.5 clks
33	36	BR negate to BG negate	tbrhgh	1.5 clks	2.5 clks





Page 3 of 13

. The state semiconductor, lnc. $MC68302\ Document$

#	Spec No.	Description	Spec Name UM	33MHz Min	33MHz Max
34	37	BGACK assert to BG negate	tgalgh	2.5 clks	4.5 clks
35	37A	BGACK assert to BR negate	tgalbrh	10 ns	1.5 clks
36	38	BG assert to Addr, Data, etc. hi-z	tglz	1	25
37	39	BG width negate	tgh	1.5 clks	1
38	40	BGACK assert to Address valid	tgalav	15	1
39	41	BGACK assert to AS assert	tgalasa	ı	20
40	44	AS, DS negate to AVEC negate	tshvph	0	25
41	46	BGACK width low	tgal	1.5 clks	1.5 clks
42	47	Async input setup time	tasi	7	1
43	48	BERR assert to DTACK assert	tbeldal	7	-
44	53	Data-out hold from clk high	tchdoi	0	ı
45	55	R/W assert to Data bus impedance change	trldbd	0	-
46	56	HALT/RESET pulse width	thrpw	10 clks	-
47	57	BGACK negate to AS, DS, RW driven	tgasd	1.5 clks	ı
48	57A	BGACK negate to FC	tgafd	1 clk	T.
49	58	BR negate to AS, DS, RW driven	trhsd	1.5 clks	1
50	58A	BR negate to FC	trhfd	1 clk	



58

59

61

62

60

57

56

55

54

53

52

. The state of the second conductor, the second second conduction of the second conductor, the second conductor is a second conductor. The second conductor is a second conductor of the second conductor is a second conductor. The second conductor is a second conductor of the second conductor is a second conductor of the seco

Table 1:

March 20, 1997 5:12 pm

51

#

61 89 88 87 86 85 83 82 4 84 81 80 62 60 63 Spec No. BR hi-z to BG high Clock high to BR hi-z DREQ low to BR low DREQ width low DREQ asynchronous set up time Clock high to RMC negate Clock low to RMC assert Clock high to BCLRO hi-z BG low to BGACK low AS and BGACK high to BGACK low Clock high to BGACK low BGACK low to BR hi-z Clock high to BR low RMC negate to BG assert Clock high to BCLR assert Description trhbgh tbglbkl tabhbkl tchbkl tbklbrz tchbrz treqlbrl treql treqasi trmhgl tclrml tchbcn tchbca tchbrl tchrmh Spec Name MU **1.5** clks 33MHz 1.5 clks clks 10 15 0 2.5 clks 2.5 clks 33MHz 2 clks 20 ns 20 ns Max 15 15 17 17 15 15 15 15

65

2

63





Page 5 of 13

. The state semiconductor, lnc. $MC68302\ Document$

#	Spec No.	Description	Spec Name UM	33MHz Min	33MHz Max
66	06	Clock on which BGACK low to clock on which AS low	tclbklal	2 clks	2 clks
67	91	Clock high to BGACK high	tchbkh	1	15
68	92	Clock low to BGACK hi-z	tclbkz	ı	10
69	93	Clock high to DACK low	tchackl	ı	15
70	94	Clock low to DACK high	tclackh	ı	15
71	95	Clock high to DONE low (output)	tchdnl	ı	15
72	96	Clock low to DONE hi-z	tcldnz	ı	15
73	97	DONE input low to clock high	tdnltch	10	-
74	100	RW valid to DS low	trwvdsl	0	-
75	101	DS low to Data-in valid	tdsldiv	ı	15
76	102	DTACK low to Data in hold time	tdkldh	0	-
77	103	AS valid to DS low	tasvdsl	0	-
78	104	DTACK low to AS, DS high	tdkldsh	0	ı
79	105	DS high to DTACK high	tdshdkh	1	25
80	106	DS inactive to AS inactive	tdsiasi	0	-
81	107	DS high to RW high	tdshrwh	0	-
82	801	DS high to data hi-z	tdshdz	ı	25





ige o of 12

. The scale Semiconductor, Inc. $MC68302\ Document$

Table 1:

March 20, 1997 5:12 pm

99 97 93 91 87 98 96 95 94 92 90 89 86 85 84 83 88 # 119 118 115 114 110 116 113 117 124 121 109A 108A 122 123 120 Spec No. DTACK high to DTACK hi-z Clock low to DTACK low (1 wait state) RW valid to clock high Clock low to UDS/LDS high Data out valid to DTACK low AS low to DTACK low (0 wait states) AS high to IAC low Clock high to RW high UDS/LDS low to clock high AS inactive time AS high to address hold time on write Clock low to AS high AS low to clock high Address valid to AS low AS high to DTACK high AS low to IAC high DS high to data out hold time Description tdthdtz tasliah tchrwh tashah tavasl tdovdkl tdshdh tcldtl tasldtl tashial tclsh tslch tash tclash taslch tashdth trwvch Spec Name MU 33MHz 21 clk 10 15 0 15 ∞ 0 33MHz Max 20 25 21 21 20 15 20 10





Page 7 of 13

. The state semiconductor, lnc. $MC68302\ Document$

abie 1:

#	Spec No.	Description	Spec Name UM	33MHz Min	33MHz Max
100	125	Clock high to data out valid	tchdov	1	15
101	126	AS high to data hi-z	tashdz	1	25
102	127	AS high to data out hold time	tashdoi	0	ı
103	128	AS high to address hold time on read	tashai	0	ı
104	129	UDS/LDS inactive time	tsh	1 clk	ı
105	130	Data in valid to clock low	tcldiv	15	ı
106	131	Clock low to data in hold time	tcldih	10	ı
107	140	Clock high to IAC high	tchiah	1	21
108	141	Clock low to IAC low	tclial		21
109	142	Clock high to DTACK low	tchdtl	,	25
110	143	Clock low to DTACK high	tcldth	•	22
111	144	Clock high to data out valid	tchdov	ı	15
112	145	AS high to data out hold time	tashdoh	0	I
113	150	Clock high to CS, IACK low	tchcsiakl	0	20
114	151	Clock low to CS, IACK high	tclcsiakh	0	20
115	152	CS width negated	tcsh	30	ı
116	153	Clock high to DTACK low (0 wait states)	tchdtkl	1	25





Page 8 of 1

. The state semiconductor, lnc. $MC68302\ Document$

abie 1:

#	Spec No.	Description	Spec Name UM	33MHz Min	33MHz Max
117	154	Clock low to DTACK low (1-6 wait states)	tcldtkh	ı	15
118	155	Clock low to DTACK high	tcldtkh	1	20
119	156	Clock high to BERR low	tchberl	1	20
120	157	Clock low to BERR hi-z	tclberh	1	20
121	158	DTACK high to DTACK hi-z	tdtkhdtkz	1	10
122	160	AS low to CS low	taslcsl	1	16
123	161	AS high to CS high	tashcsh	1	16
124	162	Address valid to AS low	tavasl	8	ı
125	163	RW valid to AS low	trwvasl	8	ı
126	164	AS negated to address hold time	tashai	0	ı
127	165	AS low to DTACK low (0 wait states)	tasldtkl	1	25
128	167	AS high to DTACK high	tashdtkh	1	18
129	891	AS low to BERR low	taslberl	ı	18
130	169	AS high to BERR hi-z	tashberh	ı	18
131	171	Input data hold time from S6 low	tidhcl	5	ı
132	172	CS negated to data out invalid (write)	tcsndoi	7	1
133	173	Address, FC valid to CS asserted	tafvcsa	15	1





. The state semiconductor, lnc. $MC68302\ Document$

#	Spec No.	Description	Spec Name UM	33MHz Min	33MHz Max
134	174	CS negated to address, FC invalid	tcsnafi	12	
135	175	CS low time (0 wait states)	tcslt	60	•
136	176	CS negate to RW invalid	tcsnrwi	7	'
137	177	CS assert to RW low (Write)	tcsarwl	ı	8
138	178	CS negate to data in invalid	tcsndii	0	'
139	180	Input data setup time	tdsu	14	-
140	181	input data hold time	tdh	ı	19
141	182	Clock high to data out valid	tchdov	1	20
142	190	Interrupt Pulse Width low IRQ	tipw	28	•
143	191	Minimum time between active edges	taemt	3 clks	-
144	200	Timer input capture pulse width	ttpw	28	-
145	201	TIN clock low pulse width	tticlt	28	•
146	202	TIN clock high pulse width and input capture high pulse width	tticht	2 clks	•
147	203	TIN clock cycle time	tcyc	3 clks	ı
148	204	Clock high to TOUT valid	tchtov	ı	24
149	205	FRZ input setup time (to clock high)	tfrzsu	14	ı
150	206	FRZ input setup time (from clock high)	tfrzht	7	





Page 10 of 13

. The state semiconductor, Inc. $MC68302\ Document$

inte 1:

1	20 L1CLKS		Time between successive IDL syncs	271	167
1	26		L1RXD hold time (from L1CLK falling edge)	270	166
ı	26		L1RXD setup time (to L1CLK falling edge)	269	165
26	0		L1TXD to hi-z (from L1CLK rising edge)	268	164
40	0		L1TXD active delay (from L1CLK falling edge)	267	163
ı	0		L1SY1 (sync) inactive before 4th L1CLK	266	162
ı	28		L1SY1 (sync) hold time (to L1CLK falling edge)	265	161
1	15		L1SY1 (sync) setup time (to L1CLK falling edge)	264	160
12	ı		L1TXD, L1RQ, SDS1-SDS2 rise/fall time	263	159
ı	P+10		L1CLK width high	262	158
ı	28		L1CLK width low	261	157
13.3 MHz	ı		L1CLK (IDL Clock) frequency	260	156
ı	6		SCP receive hold time	254	155
ı	20		SCP receive setup time	253	154
20	0		Delay from SPCLK to transmit	252	153
6	0		SPCLK clock output rise/fall time	251	152
64 clks	4 clks		SPCLK clock output period	250	151
33MHz Max	33MHz Min	Spec Name UM	Description	Spec No.	#



Page 11 of 13

. The state semiconductor, Inc. $MC68302\ Document$

	14		L1RXD Setup time to L1CLK rising edge	287	184
55	0		L1TXD active delay (from L1SY1 rising edge)	286	183
55	0		L1TxD active delay (from L1ClK rising edge)	285	182
1	26		L1SY1 sync hold time (from L1CLK falling edge)	284	181
1	15		L1SY1 sync setup time to L1CLK falling edge	283	180
1	ı		L1CLK rise/fall time MUX mode	282	179
1	P+10		L1CLK width high MUX mode	281A	178
-	55		L1CLK width low/high MUX mode	281	177
-	150		L1CLK clock period MUX mode	280	176
-	-		L1CLK rise/fall time Normal mode	282	175
1450	840		L1CLK width low/high normal mode	281	174
2100	1800		L1CLK clock period normal mode	280	173
40	7		SDS1-SDS2 inactive delay from L1CLK falling edge	276	172
40	7		SDS1-SDS2 active delay from L1CLK rising edge	275	171
-	26		L1GR hold time (from L1SY1 falling edge)	274	170
1	26		L1GR setup time (to L1SY1 falling edge)	273	169
1	1 L1CLKS		L1RQ valid before falling edge of L1SY1	272	168
33MHz Max	33MHz Min	Spec Name UM	Description	Spec No.	#





Page 12 of 13

. The state semiconductor, lnc. $MC68302\ Document$

abie 1:

#	Spec No.	Description	Spec Name UM	33MHz Min	33MHz Max
185	288	L1RXD hold time from L1CLK rising edge		26	1
186	289	Time between successive L1SY1		64 L1CLK 192 L1CLK	1 1
187	290	SDS1-SDS2 active delay from L1CLK rising edge		7	45
188	291	SDS1-SDS2 active delay from L1SY1 rising edge		7	45
189	292	SDS1-SDS2 inactive delay from L1CLK falling edge		7	45
190	293	GCIDCL (GCI data clock) active delay		0	26
191	300	L1CLK (PCM clock) frequency		ı	13.2 MHz
192	301	L1CLK width low		27	ı
193	301A	L1CLK width high		P+10	ı
194	302	L1SY0-L1SY1 setup time		0	•
195	303	L1SY0-L1SY1 hold time		20	•
196	304	L1SY0-L1SY1 width low		1 L1CLK	-
197	305	Time between successive sync signals		8 L1CLK	•
198	306	L1TXD data valid after L1CLK rising edge		0	40
199	307	L1TXD to hi-z (from L1CLK rising edge)		0	26
200	308	L1RXD setup time (to L1CLK falling edge)		11	1





Page 13 of 13

. Inc., Inc., $MC98302\ Document$

abie 1:

Description L1RXD hold time (from L1CL RCLK1 and TCLK1 frequency
RCLK1 and TCLK1 frequency RCLK1 and TCLK1 low RCLK1 and TCLK1 high
L1RXD hold time (from L1CLK falling edge) RCLK1 and TCLK1 frequency RCLK1 and TCLK1 low RCLK1 and TCLK1 high